АС ЭНЕРГИЯ

Модуль тиристорно-диодный
АМКН 172

V_{RSM} V	V_{RRM}, V_{DRM} V	I_{TRMS} = 275 A (maximum value for continuous operation) I_{TAV} = 172 A (sin 180; T_C = 86 °C)	
1700	1600	AMKH 172-16E	
1900	1800	AMKH 172-18E	

Symbol	Conditions	Values	Units
I_{TAV}	sin. 180; T_c = 85 (100) °C;	175 (124)	A
I_{TSM}	T_{vj} = 25 °C; 10 ms	5400	A
	T_{vj} = 125 °C; 10 ms	5000	A
i²t	T_{vj} = 25 °C; 8,3 ... 10 ms	145000	A²s
	T_{vj} = 125 °C; 8,3 ... 10 ms	125000	A²s
V_T	T_{vj} = 25 °C; I_T = 500 A	max. 1,41	V
$V_{T(TO)}$	T_{vj} = 125 °C	max. 0,83	V
r_T	T_{vj} = 125 °C	max. 1,3	mΩ
$V_{T(TO)(typ.)}$ [1)]	T_{vj} = 125 °C	0,8	V
$r_{T(typ.)}$ [1)]	T_{vj}= 125°C	1,2	mΩ
I_{DD}; I_{RD}	T_{vj} = 125 °C; V_{RD} = V_{RRM}; V_{DD} = V_{DRM}	max. 40	mA
t_{gd}	T_{vj} = 25 °C; I_G = 1 A; di_G/dt = 1 A/µs	1	µs
t_{gr}	V_D = 0,67 * V_{DRM}	2	µs
$(di/dt)_{cr}$	T_{vj} = 125 °C	max. 200	A/µs
$(dv/dt)_{cr}$	T_{vj} = 125 °C	max. 1000	V/µs
t_q	T_{vj} = 125 °C ,	typ. 175	µs
I_H	T_{vj} = 25 °C; typ. / max.	150 / 400	mA
I_L	T_{vj} = 25 °C; R_G = 33 Ω; typ. / max.	300 / 1000	mA
V_{GT}	T_{vj} = 25 °C; d.c.	min. 2	V
I_{GT}	T_{vj} = 25 °C; d.c.	min. 150	mA
V_{GD}	T_{vj} = 125 °C; d.c.	max. 0,25	V
I_{GD}	T_{vj} = 125 °C; d.c.	max. 10	mA
$R_{th(j-c)}$	cont.; per thyristor / per module	0,155 / 0,078	K/W
$R_{th(j-c)}$	sin. 180; per thyristor / per module	0,164 / 0,082	K/W
$R_{th(j-c)}$	rec. 120; per thyristor / per module	0,18 / 0,09	K/W
$R_{th(c-s)}$	per thyristor / per module	0,1 / 0,05	K/W
T_{vj}		- 40 ... + 125	°C
T_{stg}		- 40 ... + 125	°C
V_{isol}	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	3600 / 3000	V~
M_s	to heatsink	5 ± 15 %	Nm
M_t	to terminal	5 ± 15 %	Nm
a		5 * 9,81	m/s²
m	approx.	165	g

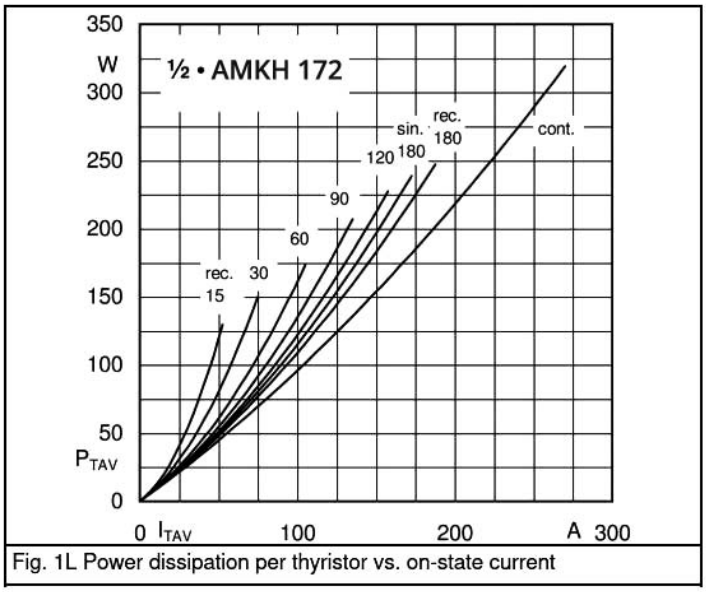


Fig. 1L Power dissipation per thyristor vs. on-state current

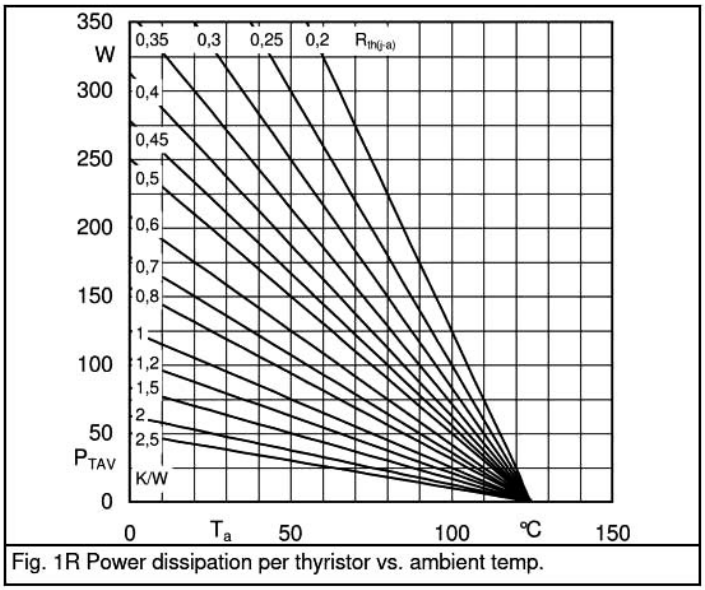


Fig. 1R Power dissipation per thyristor vs. ambient temp.

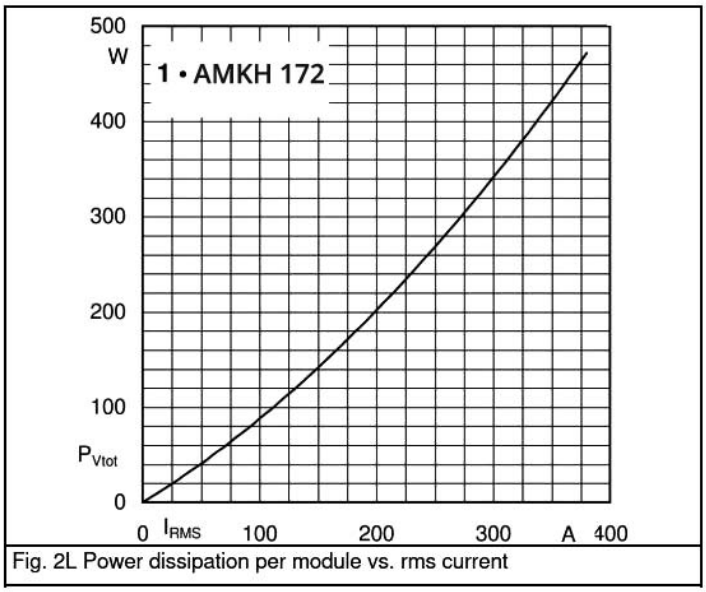


Fig. 2L Power dissipation per module vs. rms current

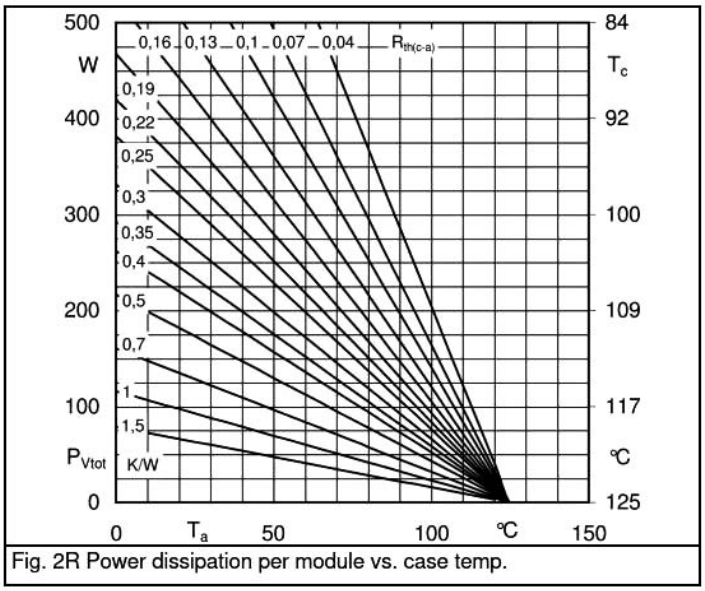


Fig. 2R Power dissipation per module vs. case temp.

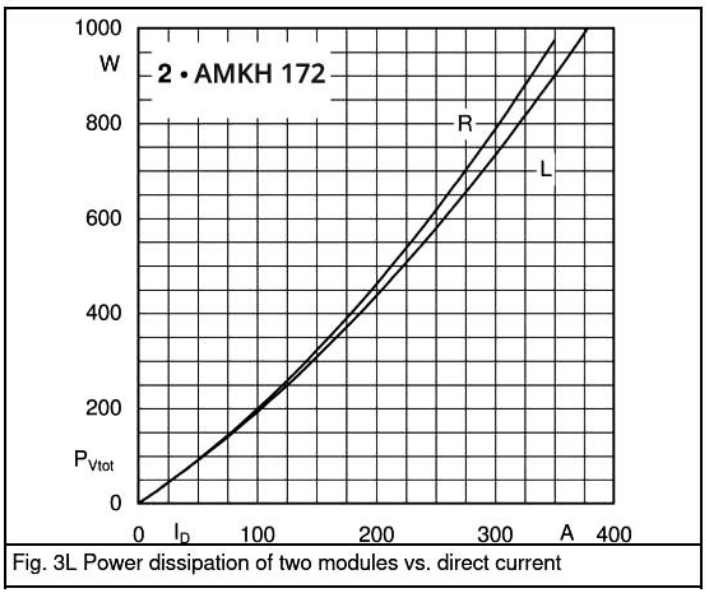


Fig. 3L Power dissipation of two modules vs. direct current

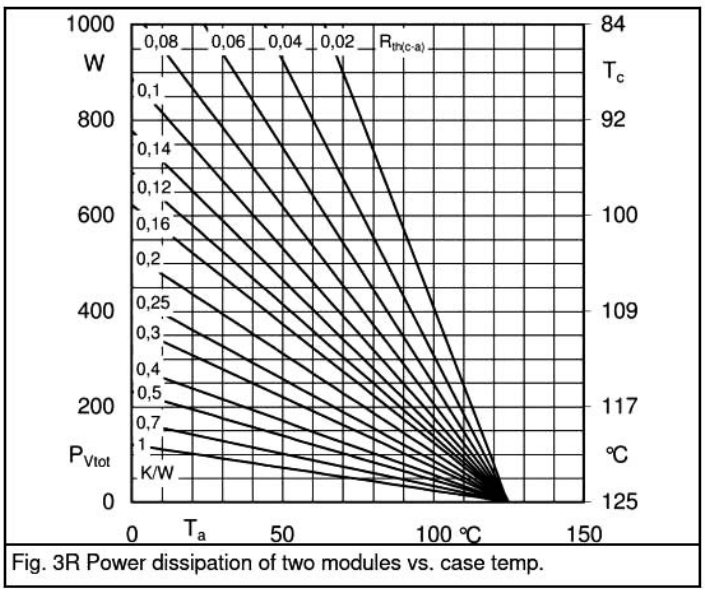


Fig. 3R Power dissipation of two modules vs. case temp.

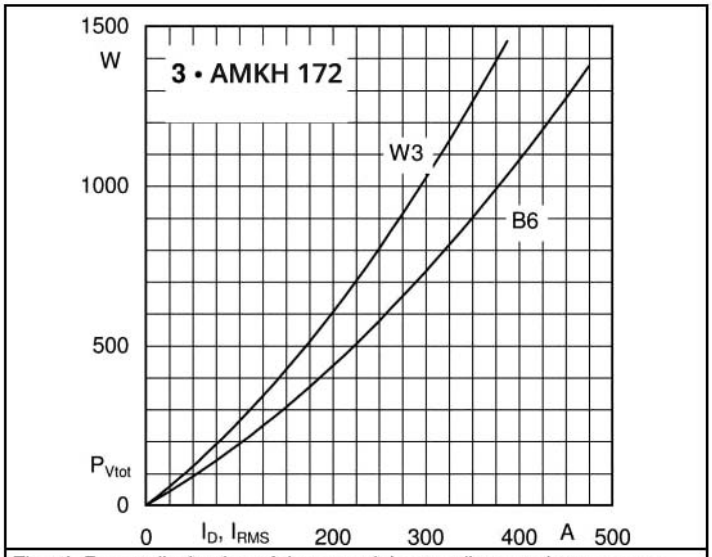


Fig. 4L Power dissipation of three modules vs. direct and rms current

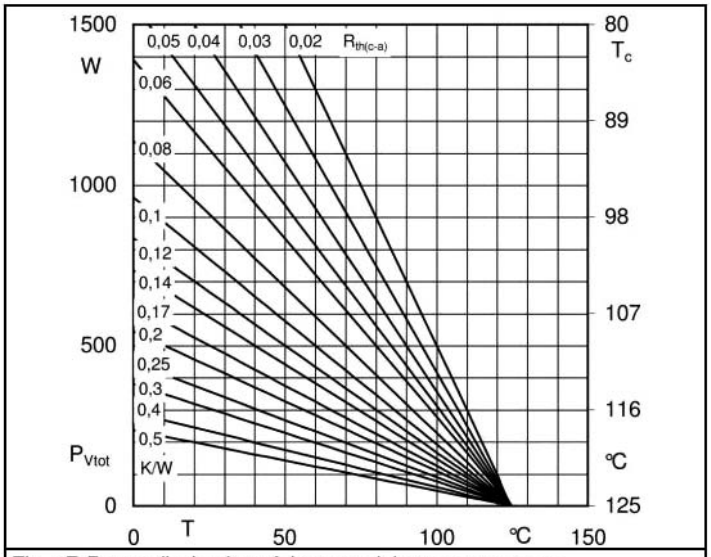


Fig. 4R Power dissipation of three modules vs. case temp.

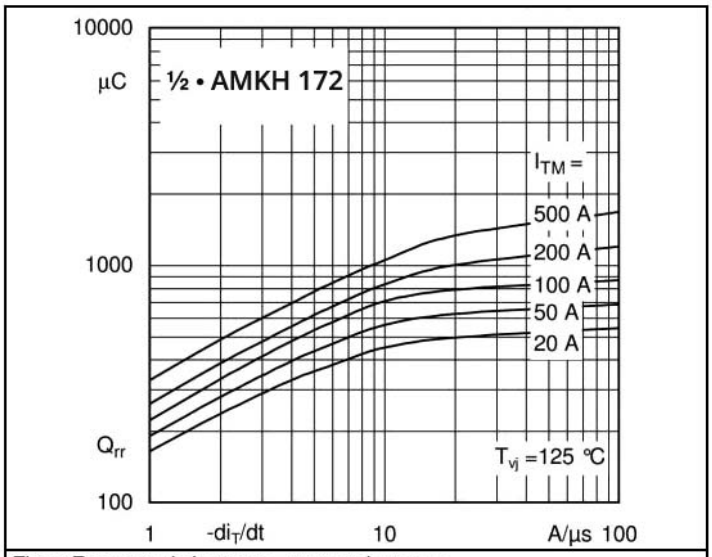


Fig. 5 Recovered charge vs. current decrease

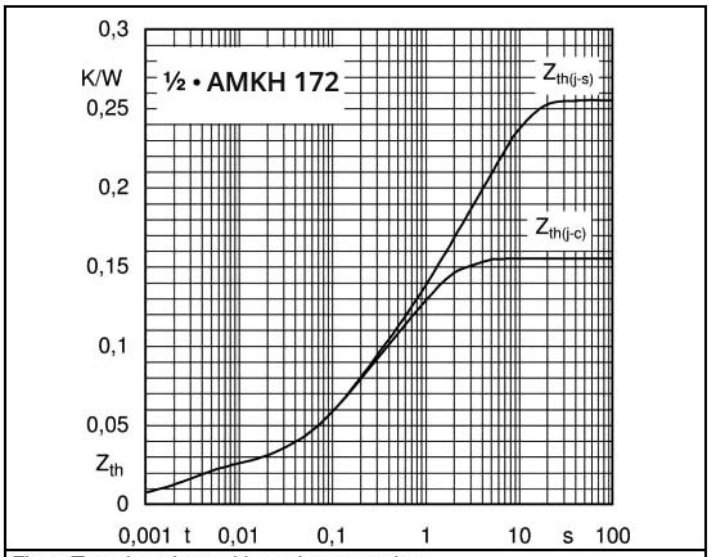


Fig. 6 Transient thermal impedance vs. time

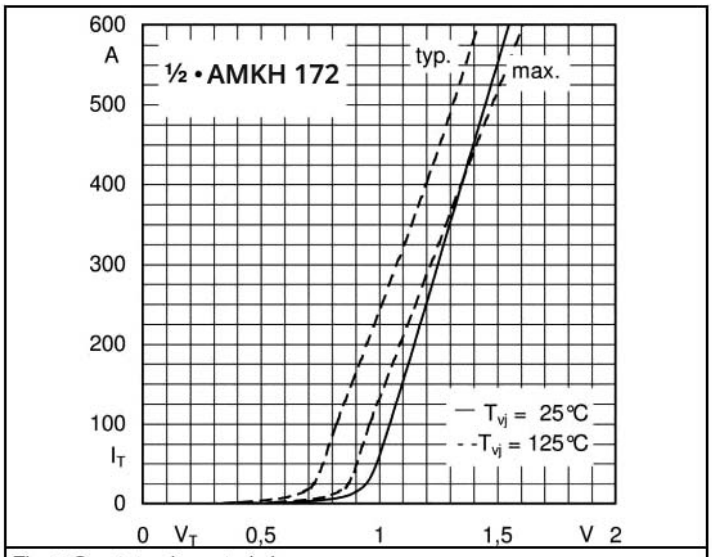


Fig. 7 On-state characteristics

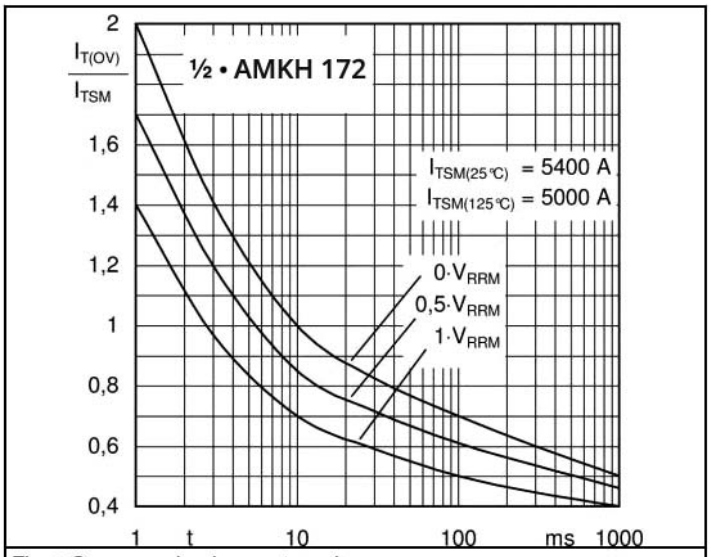


Fig. 8 Surge overload current vs. time

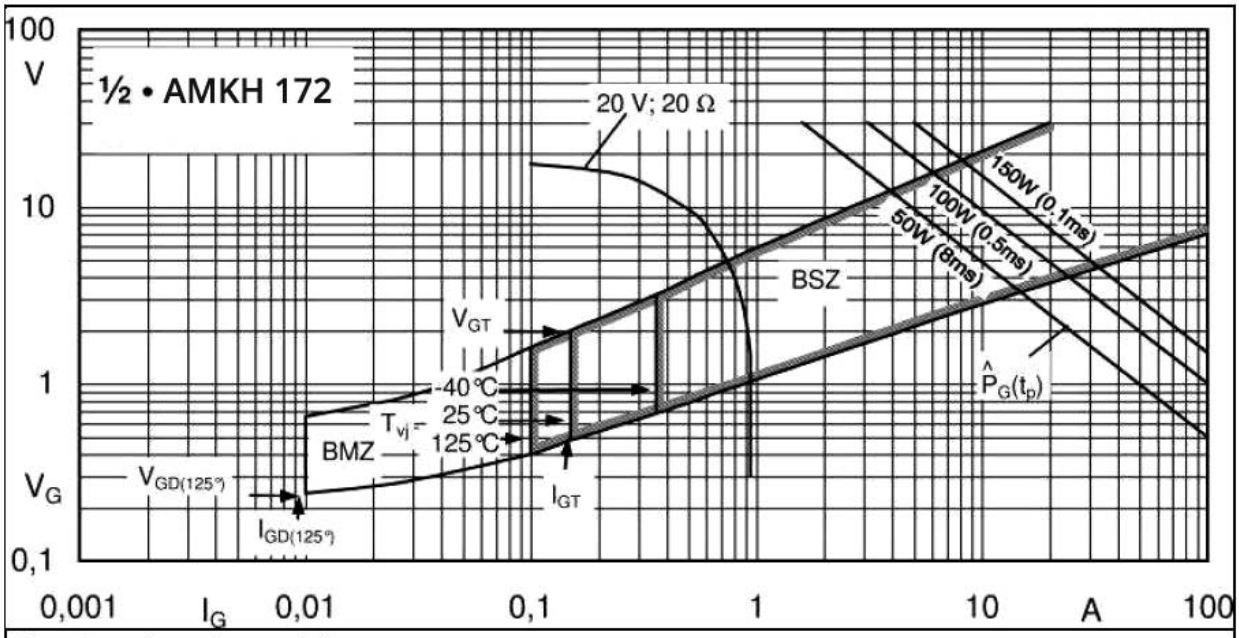
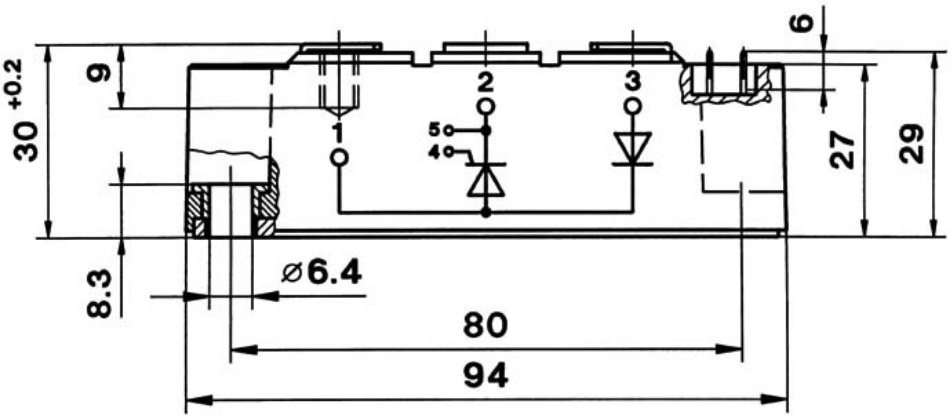
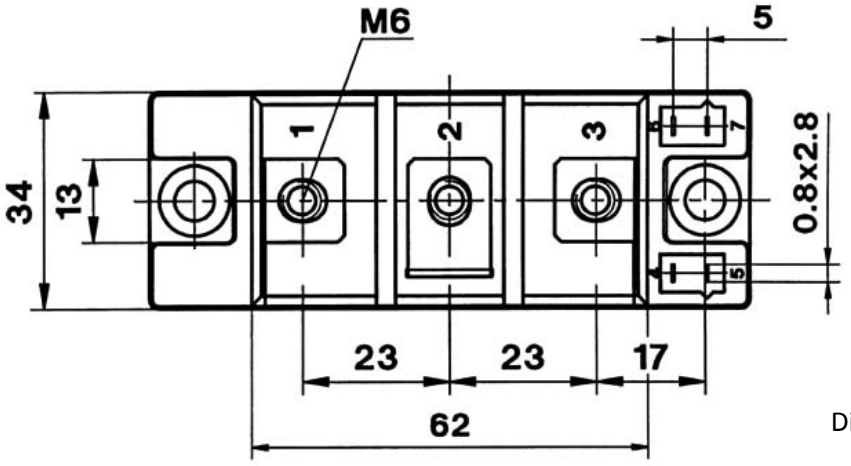
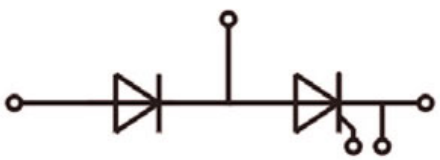


Fig. 9 Gate trigger characteristics

DIMENSIONS





Dimensions in mm

TOPOLOGY OF INTERNAL CONNECTION